# 6020K/M

## 60V N -Channel MOSFET

- **N-Channel:60V 20A**
- **RDS(on)Typ= 22mΩ@VGS = 10 V**
- **RDS(on)Typ= 29mΩ@VGS =4.5 V**

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### General Description

This Power MOSFET is produced using Maple semi's advanced TRENCH technology.

This advanced technology has been especially tailored to minimize conduction loss, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode.

### Application

- PWM Application
- Load Switch
- Power Management

### Package




Marking and pin assignment

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### Absolute Maximum Ratings ($T_C$=25℃unless otherwise specified)

| Symbol | Parameter | SLD20N06T | Units |
|---|---|---|---|
| $V_{DSS}$ | Drain-Source Voltage | 60 | V |
| $I_D$ | Drain Current - Continuous (TC= 25℃) | 20 | A |
| | - Continuous (TC= 100℃) | 14 | A |
| $I_{DM}$ | Drain Current - Pulsed (Note 1) | 60 | A |
| $V_{GSS}$ | Gate-Source Voltage | ±20 | V |
| $E_{AS}$ | Single Pulsed Avalanche Energy | 70 | mJ |
| $P_D$ | Power Dissipation (TC = 25℃) | 44 | W |
| $R_{\theta JC}$ | Thermal Resistance, Junction to Case | 2.79 | ℃/W |
| $T_J$, $T_{STG}$ | Operating and Storage Temperature Range | -55 to +150 | ℃ |
| $T_L$ | Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds | 300 | ℃ |

* Drain current limited by maximum junction temperature.

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